AMENDMENTS TO THE ABSTRACT

Please amend the abstract as shown on the attached separate page.

Abstract

A negative resist composition includes a polymer having any one of dicarboxylate monoester compounds represented by the following general formulae (1) and (2) as a monomer component:

$$O \longrightarrow R_1$$
 R_5
 $O \longrightarrow R_2$
 $O \longrightarrow R_2$
 $O \longrightarrow R_3$
 $O \longrightarrow R_3$

HO
$$R_1 \qquad R_4$$

$$R_5 \qquad R_2 \qquad (2)$$

$$OR_3$$

wherein, R_1 and R_2 represent alkyl chains having 0 to [[5]] $\underline{8}$ carbon atoms, R_3 represents a substituent having at least two or more alicyclic structures, and R_4 and R_5 represent hydrogen atoms or alkyl groups having 1 to 8 carbon atoms. A method for forming a resist pattern uses the above negative resist composition. By containing the polymer, a resistance to dry etching and a resistance to electron beam from a scanning electron microscope (SEM) are enhanced as well as a solubility in an alkali developing solution is maintained.